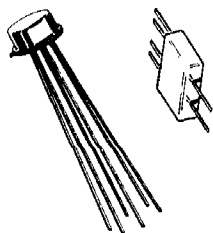


MD3250, A, F, AF
MD3251, A, F, AF

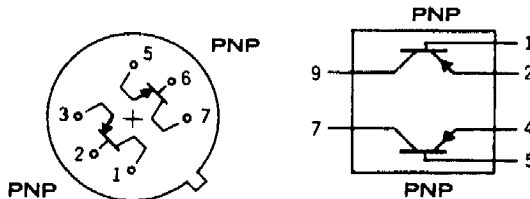
$V_{CEO} = 40V$
 $I_C = 50mA$



CASE 33
(TO-89)

Dual PNP silicon annular transistors, especially designed for low-level, differential amplifier applications.

CASE 32



PIN CONNECTIONS
(BOTTOM VIEW)

MD3250F, AF
MD3251F, AF

MAXIMUM RATINGS (each side) ($T_A = 25^\circ C$ unless otherwise noted)

Rating	Symbol	Value		Unit
		One Side	Both Sides	
Collector-Base Voltage	V_{CB}	50		Vdc
Collector-Emitter Voltage	V_{CEO}	40		Vdc
Emitter-Base Voltage	V_{EB}	5		Vdc
DC Collector Current	I_C	50		mAdc
Junction Temperature	T_J	+200		$^\circ C$
Storage Temperature Range	T_{stg}	-65 to +200		$^\circ C$
Total Device Dissipation @ $T_A = 25^\circ C$ TO-5 Case Derate above $25^\circ C$ Flat Pack Derate above $25^\circ C$	P_D	500	600	mW
		2.9	3.4	mW/ $^\circ C$
		250	350	mW
		1.5	2.0	mW/ $^\circ C$
Total Device Dissipation @ $T_C = 25^\circ C$ TO-5 Case Derate above $25^\circ C$	P_D	1.2	2.0	mW
		6.85	11.42	mW/ $^\circ C$



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

MD3250, A, F, AF and MD3251, A, F, AF (continued)

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage ($I_C = 10 \mu\text{Adc}$, $I_E = 0$)	BV_{CBO}	50	—	—	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 10 \text{ mAdc}$, $I_B = 0$)	BV_{CEO}	40	70	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10 \mu\text{Adc}$, $I_C = 0$)	BV_{EBO}	5	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 50 \text{ Vdc}$, $I_E = 0$) ($V_{CB} = 50 \text{ Vdc}$, $I_E = 0$, $T_A = 150^\circ\text{C}$)	I_{CBO}	—	—	0.01 10	μAdc
Emitter Cutoff Current ($V_{EB} = 3 \text{ Vdc}$, $I_C = 0$)	I_{EBO}	—	—	20	nAdc

ON CHARACTERISTICS

DC Forward Current Transfer Ratio* ($I_C = 10 \mu\text{Adc}$, $V_{CE} = 5 \text{ Vdc}$) ($I_C = 100 \mu\text{Adc}$, $V_{CE} = 5 \text{ Vdc}$) ($I_C = 100 \mu\text{Adc}$, $V_{CE} = 5 \text{ Vdc}$, $T_A = -55^\circ\text{C}$) ($I_C = 1 \text{ mAdc}$, $V_{CE} = 5 \text{ Vdc}$) ($I_C = 10 \text{ mAdc}$, $V_{CE} = 5 \text{ Vdc}$) ($I_C = 50 \text{ mAdc}$, $V_{CE} = 5 \text{ Vdc}$)	MD3250, MD3250A MD3251, MD3251A MD3250, MD3250A MD3251, MD3251A MD3250, MD3250A MD3251, MD3251A MD3250, MD3250A MD3251, MD3251A MD3250, MD3250A MD3251, MD3251A	h_{FE}^*	25 50 50 100 25 50 50 100 50 100 15 30	— — — — — — — — — — — —	— — — — — — — — — — — —	— — — — — — — — — — — —	— — — — — — — — — — — —
Collector-Emitter Saturation Voltage* ($I_C = 10 \text{ mAdc}$, $I_B = 1.0 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}$, $I_B = 5 \text{ mAdc}$)		$V_{CE(sat)}^*$	— —	— —	0.25 0.50	Vdc	
Base-Emitter Saturation Voltage* ($I_C = 10 \text{ mAdc}$, $I_B = 1.0 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}$, $I_B = 5 \text{ mAdc}$)		$V_{BE(sat)}^*$	0.6 —	— —	0.9 1.2	Vdc	

SMALL SIGNAL CHARACTERISTICS

Current-Gain - Bandwidth Product ($I_C = 10 \text{ mAdc}$, $V_{CE} = 20 \text{ Vdc}$, $f = 100 \text{ MHz}$)	MD3250, MD3250A MD3251, MD3251A	f_T	200 250	— —	— —	MHz
Output Capacitance ($V_{CB} = 5 \text{ Vdc}$, $I_E = 0$, $f = 100 \text{ kHz}$)		C_{ob}	—	—	6	pF
Input Capacitance ($V_{BE} = 0.5 \text{ Vdc}$, $I_C = 0$, $f = 100 \text{ kHz}$)		C_{ib}	—	—	8	pF
Small Signal Current Gain ($I_C = 1.0 \text{ mA}$, $V_{CE} = 10 \text{ V}$, $f = 1 \text{ kHz}$)	MD3250, MD3250A MD3251, MD3251A	h_{fe}	50 100	— —	200 400	—
Voltage Feedback Ratio ($I_C = 1.0 \text{ mA}$, $V_{CE} = 10 \text{ V}$, $f = 1 \text{ kHz}$)	MD3250, MD3250A MD3251, MD3251A	h_{re}	— —	— —	10 20	$\times 10^{-4}$
Input Impedance ($I_C = 1.0 \text{ mA}$, $V_{CE} = 10 \text{ V}$, $f = 1 \text{ kHz}$)	MD3250, MD3250A MD3251, MD3251A	h_{ie}	1 2	— —	6 12	kohms
Output Admittance ($I_C = 1.0 \text{ mA}$, $V_{CE} = 10 \text{ V}$, $f = 1 \text{ kHz}$)	MD3250, MD3250A MD3251, MD3251A	h_{oe}	4 10	— —	40 60	μmhos
Wide Band Noise Figure ($I_C = 100 \mu\text{A}$, $V_{CE} = 10 \text{ V}$, $R_g = 3 \text{ kohm}$, Noise Bandwidth 10 cps to 15.7 kHz)	MD3250, MD3250A MD3251, MD3251A	NF	— —	— —	4 3	dB

MATCHING CHARACTERISTICS (Types MD3250A and MD3251A only)

DC Current Gain Ratio** ($I_C = 100 \mu\text{Adc}$ and 1 mAdc , $V_{CE} = 5 \text{ Vdc}$)	MD3250A, MD3251A	h_{FE1}/h_{FE2}^{**}	0.9	—	1.0	—
Base Voltage Differential ($I_C = 10 \mu\text{A}$, to 10 mA , $V_{CE} = 5 \text{ Vdc}$) ($I_C = 100 \mu\text{Adc}$, $V_{CE} = 5 \text{ Vdc}$)	MD3250A, MD3251A MD3250A, MD3251A	$ V_{BE1} - V_{BE2} $	— —	— —	5 3	mVdc
Base Voltage Differential Change ($I_C = 100 \mu\text{Adc}$, $V_{CE} = 5 \text{ Vdc}$, $T_A = -55$ to $+25^\circ\text{C}$) ($I_C = 100 \mu\text{Adc}$, $V_{CE} = 5 \text{ Vdc}$, $T_A = 25$ to 125°C)	MD3250A, MD3251A MD3250A, MD3251A	$\Delta(V_{BE1} - V_{BE2})$	— —	— —	0.8 1.0	mVdc

*Pulse Test $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$

** The lowest h_{FE} reading is taken as h_{FE1} for this ratio